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Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (previously amended) A process for forming a resist pattern, which increases the amount of reduction in thickness of a chemically amplified positive photoresist coating after development by 100 Å to 600 Å in comparison with the case of not applying the composition for preventing development-defects, comprising: a step of forming a chemically amplified positive photoresist coating on a substrate having a diameter of 8 inches or more by application; a step of applying a composition for preventing development-defects containing a surfactant on the chemically amplified positive photoresist coating; a step of baking after at least either the step of forming the chemically amplified positive photoresist coating by application or the step of applying the composition for preventing development-defects; a step of selectively exposing the chemically amplified positive photoresist coating; a step of post-exposure baking the chemically amplified positive photoresist coating; and a step of developing the chemically amplified positive photoresist coating, wherein said surfactant is at least one member selected from the group consisting of (1) a tetraalkylammonium salt of C₄ to C₁₅ perfluoroalkylcarboxylic acid and (2) a tetraalkylammonium salt of C₄ to C₁₀ perfluoroalkylsulfonic acid, at the same time said surfactant being one that is formed at the equivalent ratio of acid to base of 1:1.04 ~ 1:3, and further where the composition for preventing development-defects has an equivalent excess of base as compared to acid.
2. (canceled)